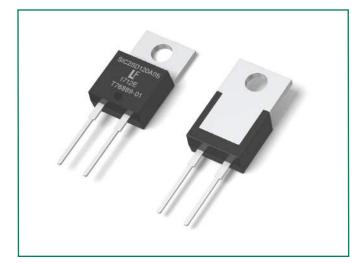
GEN2 SiC Schottky Diode LSIC2SD120A05, 1200 V, 5 A, TO-220-2L

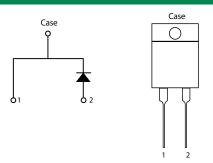


LSIC2SD120A05

HF RoHS 🔞



Circuit Diagram TO-220-2L



Description

This series of silicon carbide (SiC) Schottky diodes has negligible reverse recovery current, high surge capability, and a maximum operating junction temperature of 175 °C. These diodes series are ideal for applications where improvements in efficiency, reliability, and thermal management are desired.

Features

- Positive temperature coefficient for safe operation and ease of paralleling
- 175 °C maximum operating junction temperature
- Excellent surge capability

Applications

- Boost diodes in PFC or DC/DC stages
- Switch-mode power supplies
- Uninterruptible power supplies
- Solar inverters

diodes

Extremely fast,

switching behavior

• Dramatically reduced

compared to Si bipolar

switching losses

temperature-independent

- Industrial motor drives
- EV charging stations

Environmental

- Littelfuse "RoHS" logo = RoHS RoHS conform
- Littelfuse "HF" logo = **HF** Halogen Free
- Littelfuse "PB-free" logo = PB-free lead plating

| Maximum | Ratings |
|---------|---------|
|---------|---------|

| Maximum natings | | | | |
|-------------------|--|--|---|--|
| Symbol | Conditions | Value | Unit | |
| V _{RRM} | - | 1200 | V | |
| V _R | T _i = 25 °C | 1200 | V | |
| | T _c = 25 °C | 17.5 | | |
| I _F | T _c = 135 °C | 8.5 | A | |
| | T _c = 158 °C | 5 | | |
| I _{FSM} | $T_c = 25 \text{ °C}, T_p = 10 \text{ ms}, \text{ Half sine pulse}$ | 40 | A | |
| P _{Tot} | $T_c = 25 \text{ °C}$ | 100 | W | |
| | T _c = 110 °C | 43.3 | | |
| TJ | - | -55 to 175 | °C | |
| T _{stg} | - | -55 to 150 | °C | |
| T _{sold} | - | 260 | °C | |
| | V _{RRM} V _R I _F P _{Tot} T _J T _{STG} | $\begin{array}{c c} V_{\text{RRM}} & - & \\ V_{\text{R}} & T_{\text{j}} = 25 \ ^{\circ}\text{C} \\ & \\ I_{\text{F}} & \frac{T_{\text{c}} = 25 \ ^{\circ}\text{C}}{T_{\text{c}} = 135 \ ^{\circ}\text{C}} \\ \hline T_{\text{c}} = 135 \ ^{\circ}\text{C} \\ \hline T_{\text{c}} = 158 \ ^{\circ}\text{C} \\ \hline T_{\text{c}} = 158 \ ^{\circ}\text{C} \\ \hline \end{array} \\ \hline P_{\text{Tot}} & T_{\text{c}} = 25 \ ^{\circ}\text{C}, T_{\text{p}} = 10 \ \text{ms}, \ \text{Half sine pulse} \\ \hline P_{\text{Tot}} & \frac{T_{\text{c}} = 25 \ ^{\circ}\text{C}}{T_{\text{c}} = 110 \ ^{\circ}\text{C}} \\ \hline T_{\text{c}} = 110 \ ^{\circ}\text{C} \\ \hline \end{array} \\ \hline T_{\text{sTG}} & - \\ \hline \end{array} \\ \hline \end{array}$ | $\begin{array}{c c c c c c c c } & & & & & & & & & & & & & & & & & & &$ | |



Electrical Characteristics

| Characteristics | Symbol | Conditions | Value | | | |
|--------------------------------|----------------|--|-------|------|------|------|
| | | | Min. | Тур. | Max. | Unit |
| Forward Voltage V _F | M | I _F = 5 A, Τ _J = 25 °C | - | 1.5 | 1.8 | V |
| | V _F | I _F = 5 A, Τ _J = 175 °C | - | 2.1 | | V |
| Reverse Current | 1 | $V_{_{ m R}} = 1200 \text{ V}$, $T_{_{ m J}} = 25 \ ^{\circ}\text{C}$ | - | <1 | 100 | μA |
| | R | V _R = 1200 V , T _J = 175 °C | - | 5 | | |
| Total Capacitance C | | V _R = 1 V, f =1 MHz | - | 310 | | |
| | С | V _R = 400 V, f = 1 MHz | - | 29 | | pF |
| | | V _R = 800 V, f = 1 MHz | - | 21 | | |
| Total Capacitive Charge | Q _c | $V_R = 800 \text{ V}, \ Q_c = \int_0^{V_R} c(v) dv$ | - | 30 | | nC |

Footnote: $T_1 = +25$ °C unless otherwise specified

| Thermal Characteristics | | | | | | |
|-------------------------|------------------|---------------|-------|------|------|------|
| Characteristics Syml | | ol Conditions | Value | | | |
| | Symbol | | Min. | Тур. | Max. | Unit |
| Thermal Resistance | R _{ejc} | - | - | 1.50 | | °C/W |

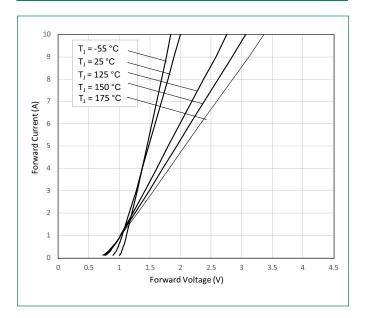
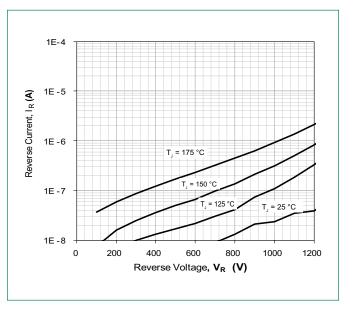


Figure 1: Typical Foward Characteristics

Figure 2: Typical Reverse Characteristics



GEN2 SiC Schottky Diode LSIC2SD120A05, 1200 V, 5 A, TO-220-2L



Figure 3: Power Derating

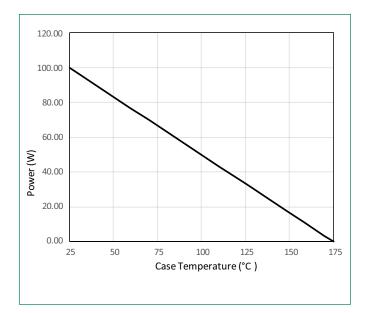


Figure 4: Current Derating

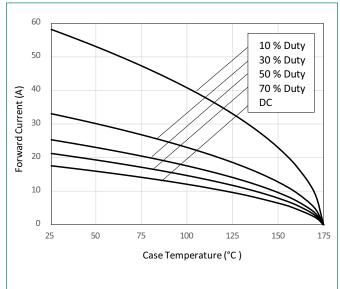


Figure 5: Capacitance vs. Reverse Voltage

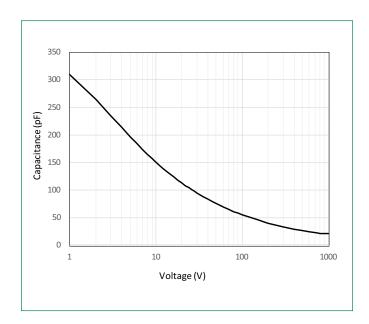


Figure 6: Capacitive Charge vs. Reverse Voltage

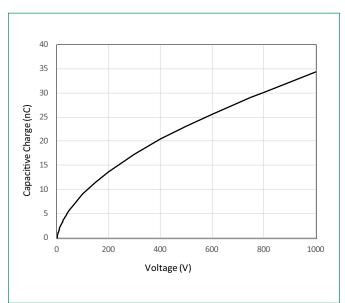




Figure 7: Stored Energy vs. Reverse Voltage

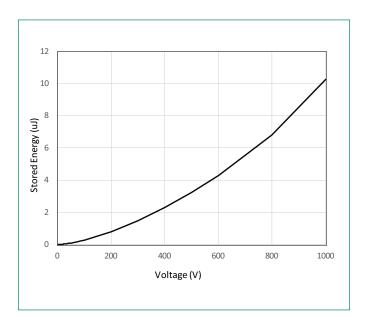
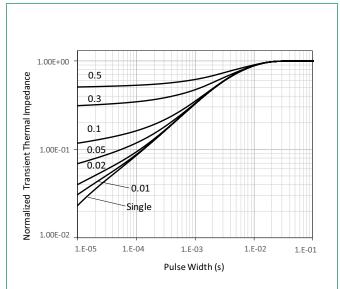
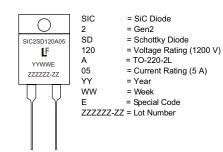


Figure 8: Transient Thermal Impedance



Part Numbering and Marking System



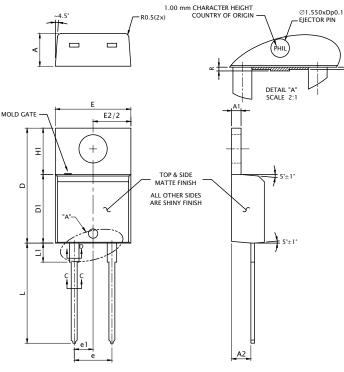
Packing Options

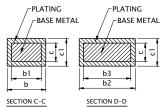
| Part Number | Marking | Packing Mode | M.O.Q |
|---------------|--------------|--------------|-------|
| LSIC2SD120A05 | SIC2SD120A05 | Tube | 1000 |

GEN2 SiC Schottky Diode LSIC2SD120A05, 1200 V, 5 A, TO-220-2L



Dimensions-Package TO-220-2L





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E1

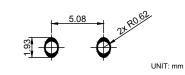
Ø

D2

| Symbol | Min | Nominal | Max |
|--------|--------|---------|--------|
| А | 4.320 | 4.450 | 4.570 |
| A1 | 1.140 | 1.270 | 1.400 |
| A2 | 2.500 | - | 2.740 |
| b | 0.690 | - | 0.880 |
| b1 | 0.680 | - | 0.870 |
| b2 | 1.230 | - | 1.390 |
| b3 | 1.220 | 1.270 | 1.380 |
| С | 0.360 | - | 0.503 |
| c1 | 0.630 | - | 0.527 |
| D | 14.900 | - | 15.600 |
| D1 | 8.615 | - | 9.017 |
| D2 | 12.840 | - | 12.950 |
| E | 10.000 | 10.180 | 10.360 |
| E1 | 7.570 | 7.610 | 7.680 |
| e1 | 2.490 | 2.540 | 2.590 |
| е | 5.030 | 5.080 | 5.130 |
| H1 | 6.295 | 6.545 | 6.795 |
| L | 13.000 | 13.500 | 14.00 |
| L1 | 2.390 | - | 3.250 |
| øP | 3.710 | 3.840 | 3.960 |
| Q | 2.650 | - | 3.050 |
| R | - | - | 0.254 |

- MOLD FLASH (Refer to notes) Millimeters

Recommended Solder Pad Layout



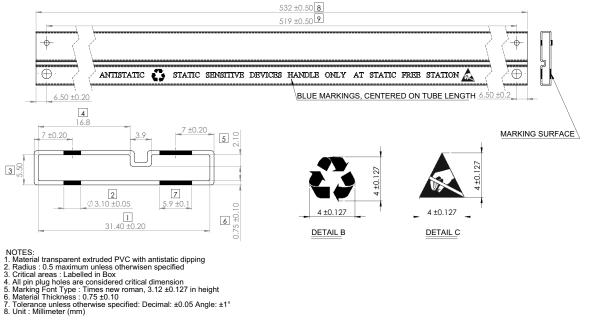
NOTES: 1. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 MM PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREME OF PLASTIC BODY.

2. DIMENSIONS E2 & H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES RE ALLOWED.

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Packing Specification (Tube for TO-220-2L)



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